

Appl. No. 09/817,967

Amdt. Dated February 9, 2004

Reply to Office Action of September 8, 2003

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks/Arguments begin on page 9 of this paper.

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-10 (canceled).

11 (currently amended). A component, which comprises:

a substrate;

a lower insulating layer having a layer thickness between 0.05 μm and 50 μm and having a region;

at least one upper insulating layer having a layer thickness between 0.05 μm and 50 μm and having a region; and

at least one activated region that is selectively activated using an activator selected from the group consisting of a gas, a liquid, a solution, and plasma ~~for a process selected from the group consisting of subsequent metallization, photosensitization, hydrophobicization and surface~~

~~functionalization that is other than metallization,~~
~~photosensitization, and hydrophobicization;~~

said at least one activated region being selected from the group consisting of said region of said lower insulating layer and said region of said at least one upper insulating layer, said activated region therefore being an activated insulating layer;

said lower insulation layer located adjacent said at least one upper insulation layer;

said activated region being one of a selectively modified region and a surface of said activated insulating layer such that subsequently only said activated region can be subjected to a process selected from a group of metallization, photosensitization, and hydrophobicization.

12 (previously presented). The component according to claim 11, wherein said substrate, said lower insulating layer, and said at least one upper insulating layer form a component selected from the group consisting of an electronic component and a microelectronic component.

13 (canceled).

14 (previously presented). The component according to claim 11, wherein said at least one said upper layer is a layer selected from the group consisting of a patterned layer and a mask layer for activating said lower layer.

15 (previously presented). The component according to claim 11, wherein said at least one activated region is a region selected from the group consisting of a seeded region and a metallized region.

16-23 (canceled).

24 (currently amended). A process for producing a component, which comprises:

in a first working step, applying a lower insulating layer having a layer thickness between 0.05 μm and 50 μm to a substrate;

in a second working step, selectively activating at least one region of the lower insulating layer using an activator selected from the group consisting of a gas, a liquid, a solution and plasma for forming an activated region being one

of a selectively modified region and a surface of the lower
insulating layer; and

in a third working step, applying at least one upper
insulating layer having a layer thickness between 0.05 μm and
50 μm and being chemically different from said at least one
lower insulating layer to the lower, activated insulating
layer and patterning the at least one upper insulating layer.

25 (previously presented). The process according to claim
24, which comprises patterning the lower insulating layer in
the first working step.

26 (previously presented). The process according to claim
24, which comprises choosing a selected layer from the group
consisting of the at least upper one insulating layer and the
lower insulating layer and patterning the selected layer
after the selected layer has been applied.

27 (currently amended). A process for producing a component,
which comprises:

in a first working step, applying a first insulating layer
having a layer thickness between 0.05 μm and 50 μm to a
substrate;

in a second working step, applying a second insulating layer having a layer thickness between 0.05 μm and 50 μm and being chemically different from said at least one lower insulating layer and patterning the second insulating layer; and

in a third working step, selectively activating a layer selected from the group consisting of the first insulating layer and the second insulating layer using an activator selected from the group consisting of a gas, a liquid, a solution, and plasma for forming an activated insulating layer, the activating step includes the step of selectively modifying a region or a surface of the activated insulating layer.

28 (previously presented). The process according to claim 27, which comprises patterning the first insulating layer in the first working step.

29 (previously presented). The process according to claim 27, which comprises patterning the second insulating layer after the second working step and before the third working step.

30 (previously presented). The process according to claim 29, which comprises patterning the first insulating layer, after the first working step.

31 (previously presented). The process according to claim 27, which comprises patterning the first insulating layer, after the first working step.